

ASDL-6770

High Performance Silicon NPN Phototransistor in Side Look Package



Data Sheet

Description

ASDL-6770 is a silicon phototransistor encapsulated in clear molded Side Look package. It has high sensitivity with low dark current and fast response time. Collector is denoted by a flat on the packaging diagram and the shorter of the two leads. This device matches with infrared emitter ASDL-4770 and is ideal for low cost, high volume applications.

Features

- Clear Side Look Package
- Wide spectral response
- High Sensitivity
- High Speed
- Low Dark Current
- Narrow Viewing Angle
- Low Cost
- Lead Free & ROHS Compliant
- Available in Tape & Reel

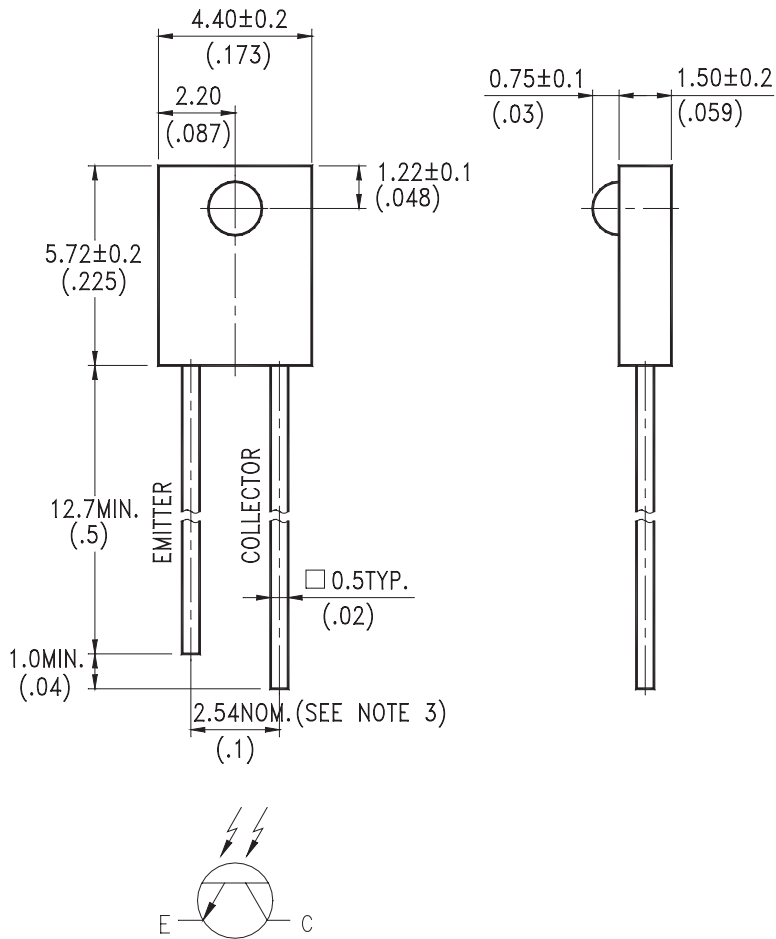
Applications

- Detector in Consumer Electronics
- Detector Industrial Electronics & Equipment
- Coin counters
- Position sensing
- IR Data Communication
- Photo Interrupter

Ordering Information

Part Number	Lead Form	Color	Packaging	Shipping Option
ASDL-6770-C22	Straight	Clear	Tape & Reel	4000pcs
ASDL-6770-C41			Bulk	20Kpcs / Carton

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches)
2. Tolerance is $+0.25$ mm ($.010$ in) unless otherwise noted
3. Lead spacing is measured where leads emerge from package
4. Specifications are subject to change without notice.

Absolute Maximum Ratings at T_A=25°C

Parameter	Symbol	Min.	Max	Unit
Power Dissipation	P _{DISS}		100	mW
Collector Emitter Voltage	V _{CEO}		30	V
Emitter Collector Voltage	V _{EC0}		5	V
Operating Temperature	T _O	-40	85	°C
Storage Temperature	T _S	-55	100	°C
Junction temperature	T _J		110	°C
Lead Soldering Temperature [.6mm (0.063") From Body]		260°C for 5 seconds		

Electrical Characteristics at 25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	30			V	I _c = 1mA Ee = 0mW/cm ²
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5			V	I _e = 100μA Ee = 0mW/cm ²
Collector Emitter Saturation Voltage	V _{CE(SAT)}			0.4	V	I _c = 0.1mA Ee = 1mW/cm ²
Collector Dark Current	I _{CEO}			100	nA	V _{CE} =10V Ee=0mW/cm ²
Thermal Resistance, Junction to Pin	Rθ _{jp}		350		°C/W	

Optical Characteristics at 25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Viewing Angle	2θ _{1/2}		40		Deg	
Wavelength of Peak sensitivity	λ _{PK}		900		nm	
Spectral BandWidth	Δλ	400	900	1100	nm	
Rise Time	t _r		10		μs	V _{CC} = 5V I _c = 1mA R _L = 1KΩ
Fall Time	t _f		15		μs	V _{CC} = 5V I _c = 1mA R _L = 1KΩ
On State Collector Current	I _{C(ON)}	1.04		2.40	mA	V _{CE} = 5V Ee = 1mW/cm ² λ = 940nm

Typical Electrical/Optical Characteristics Curves ($T_A=25^{\circ}\text{C}$ unless otherwise indicated)

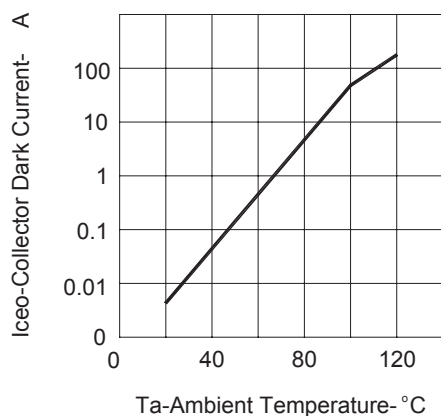


FIGURE 1. COLLECTOR DARK CURRENT VS AMBIENT TEMPERATURE

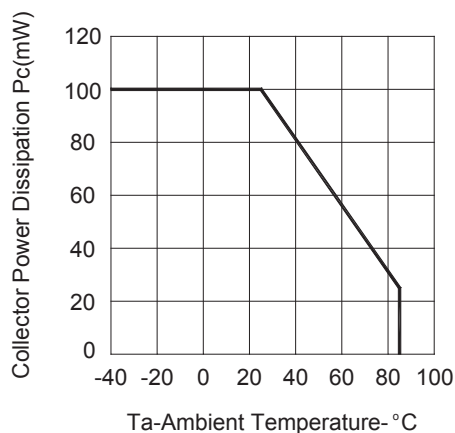


FIGURE 2. COLLECTOR POWER DISSIPATION VS AMBIENT TEMPERATURE

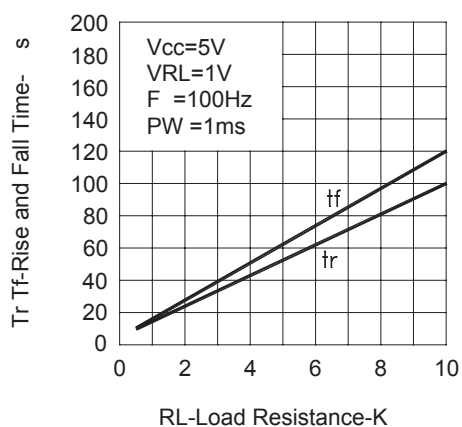


FIGURE 3. RISE AND FALL TIME VS LOAD RESISTANCE

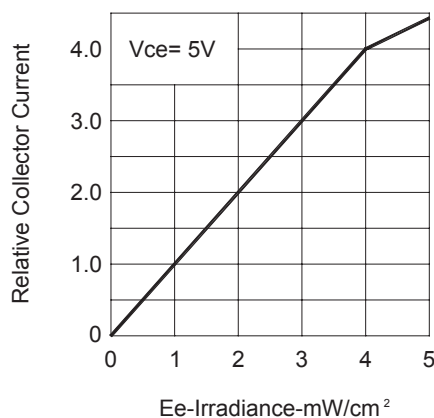


FIGURE 4. RELATIVE COLLECTOR CURRENT VS IRRADIANCE

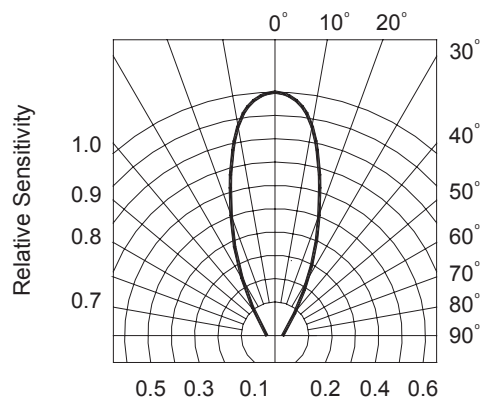


FIGURE 5. SENSITIVITY DIAGRAM

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